

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior listing of claims in this application.

Claims 1-12. (Canceled)

13. (Currently Amended) A semiconductor device comprising:

a layer that is transparent to light ~~having a wavelength of approximately 248 nm~~  
having a first thickness; and

a first continuous anti-reflective coating ~~extending substantially entirely formed~~  
beneath the ~~transparent transparent~~ layer having a second thickness, wherein said first  
thickness is greater than the second thickness.

14. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

15. (Original) The semiconductor device of claim 13 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

16. (Original) The semiconductor device of claim 13 wherein the transparent layer includes an oxide.

17. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising an organic polymer.

18. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

19. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

20. (Original) The semiconductor device of claim 13 further including:

a second anti-reflective coating extending over the transparent layer.

21. (Previously Presented) A semiconductor device comprising:

a layer that is transparent to light having a wavelength of approximately 365 nm;

and

a first anti-reflective coating extending substantially entirely beneath the transparent layer.

22. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

23. (Original) The semiconductor device of claim 21 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

24. (Original) The semiconductor device of claim 21 wherein the transparent layer includes an oxide.

25. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

26. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

27. (Original) The semiconductor device of claim 21 further including:

a second anti-reflective coating extending over the transparent layer.

28. (Previously Presented) A semiconductor device comprising:

a layer that is transparent to light having a wavelength of approximately 193 nm;  
and

a first anti-reflective coating extending substantially entirely beneath the transparent layer.

29. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

30. (Original) The semiconductor device of claim 28 wherein the transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.

31. (Original) The semiconductor device of claim 28 wherein the transparent layer includes an oxide.

32. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

33. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

34. (Original) The semiconductor device of claim 28 further including:

a second anti-reflective coating extending over the transparent layer.

35. (Previously Presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

36. (Previously Presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

37. (Previously Presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising an organic polymer.

38. (Previously Presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

39. (Previously Presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

40. (Previously Presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising an organic polymer.

41. (Previously Presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

42. (Previously Presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

43. (Previously Presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising an organic polymer.

44. (New) A semiconductor device comprising:

a silicon oxide layer formed over a surface of a substrate;  
an anti-reflective coating layer having a first thickness formed over said silicon oxide layer;

a layer which is transparent to the wavelength of light formed over the anti-reflective coating layer, said transparent layer having a second thickness greater than said first thickness.

45. (New) The semiconductor device of claim 13, wherein said transparent layer is transparent to light having a wavelength of approximately 248 nm.